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c) a first fixed potential is applied to said second impurity region and a second fixed potential higher than said first fixed potential is applied to said fourth impurity region.

REMARKS

Favorable reconsideration of the above-identified patent application in light of the foregoing amendment and following remarks is respectfully requested.

Applicants respectfully point out that the portions of the remarks provided in the October 3, 2002 Amendment not recited in the remarks of the November 26, 2002 Supplemental Amendment should be given no weight because the noted October 3, 2002 remarks include arguments not intended to be placed on the record by the Applicants. Moreover, Applicants respectfully point out that the second full paragraph on page 4 of the November 26, 2002 Supplemental Amendment should be given no weight because that argument was not intended to be included by the Applicants.

An early and favorable action is respectfully requested.

Respectfully submitted,

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IN THE CLAIMS

Please amend claim 11 as shown in the Attachment, in which underlining and bracketing show the changes introduced into the previously-pending claims to arrive at the clean claims provided below:

11. (Amended Three Times) The semiconductor device according to claim 1, wherein:

a) said first conductivity type is an n type and said second conductivity type is a p type;

b) said observation part further includes:

1) a second pn junction having a p-type third impurity region connected with said wire[;] and an n-type fourth impurity region; and

c) a first fixed potential is applied to said second impurity region and a second fixed potential higher than said first fixed potential is applied to said fourth impurity region.